

ON Semiconductor®

MJD31CE NPN Epitaxial Silicon Transistor

Features

- General-Purpose Amplifier
- Low-Speed Switching Applications
- Lead Formed for Surface Mount Application (No Suffix)
- Electrically Similar to Popular TIP31 and TIP31C

Application

- Switching Regulators
- Converters
- Power Amplifiers



Ordering Information

Part Number	Top Mark	Package	Packing Method
MJD31CETF-SN00207	MJD31CE	TO-252 3L (DPAK)	Tape and Reel
MJD31CEITU	MJD31C-I	TO-251 3L (IPAK)	Rail

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol Parameter		Value	Units	
V _{CBO}	Collector-Base Voltage	100	V	
V _{CEO}	Collector-Emitter Voltage	100	V	
V _{EBO}	Emitter-Base Voltage	5	V	
Ι _C	Collector Current (DC)	3	A	
I _{CP}	Collector Current (Pulse)	5	A	
I _B	Base Current	1	A	
P _C	Collector Dissipation (T _C =25°C)	15	W	
	Collector Dissipation (T _A =25°C)	1.56	W	
TJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 65 to +150	°C	

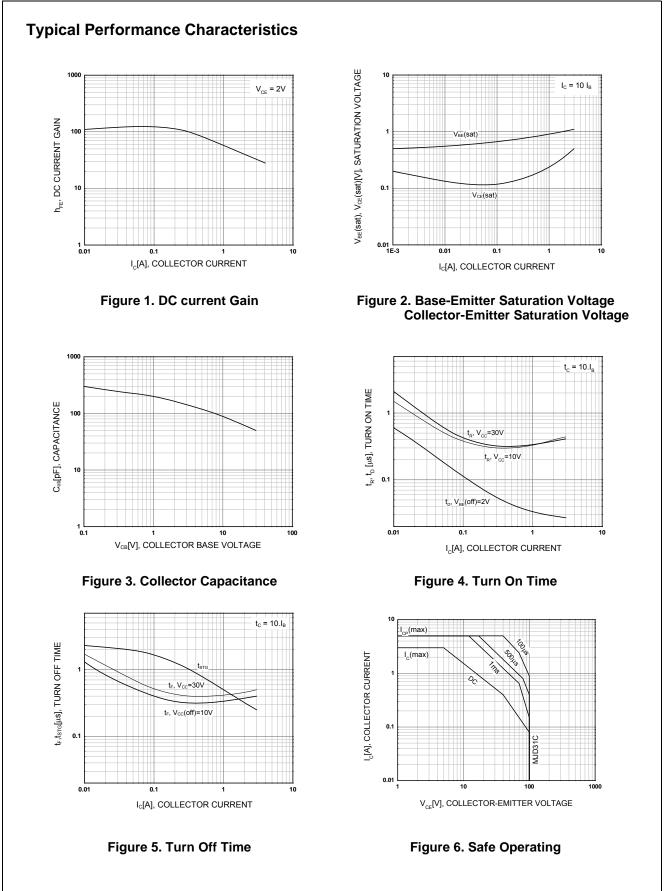
Electrical Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Units
V _{CEO} (sus)	Collector-Emitter Sustaining Volt- age ⁽¹⁾	I _C = 30 mA, I _B = 0	100		V
I _{CEO}	Collector Cut-off Current	V _{CE} = 60 V, I _B = 0		50	μA
I _{CES}	Collector Cut-off Current	V _{CE} = 100 V, V _{BE} = 0		20	μA
I _{EBO}	Emitter Cut-off Current	V _{BE} = 5V, I _C = 0		1	mA
h _{FE}	DC Current Gain ⁽¹⁾	V _{CE} = 1 V, I _C = 100 mA	60	130	
		V _{CE} = 4 V, I _C = 1 A	25		
		$V_{CE} = 4 V, I_C = 3 A$	10	50	
V _{CE} (sat)	Collector-Emitter Saturation Voltage ⁽¹⁾	I _C = 3 A, I _B = 375 mA		1.2	V
V _{BE} (on)	Base-Emitter On Voltage ⁽¹⁾	V _{CE} = 4 A, I _C = 3 A		1.8	V
f _T	Current Gain Bandwidth Product	V _{CE} = 10 V, I _C = 500 mA	3		MHz

Note:

1. Pulse test : $pw \le 300 \ \mu s$, duty cycle $\le 2\%$.



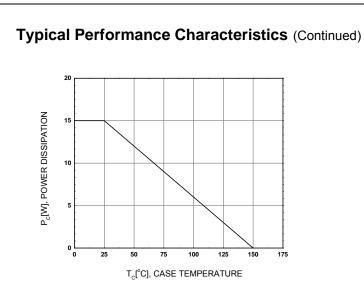
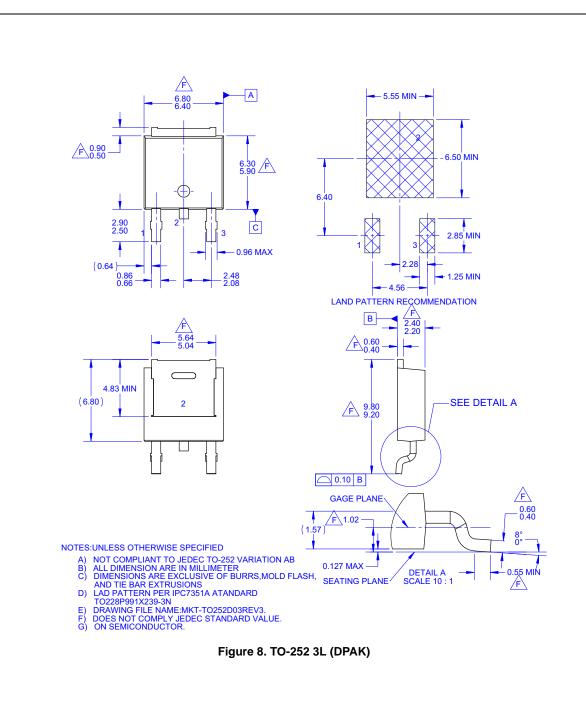


Figure 7. Power Derating

MJD31CE — NPN Epitaxial Silicon Transistor



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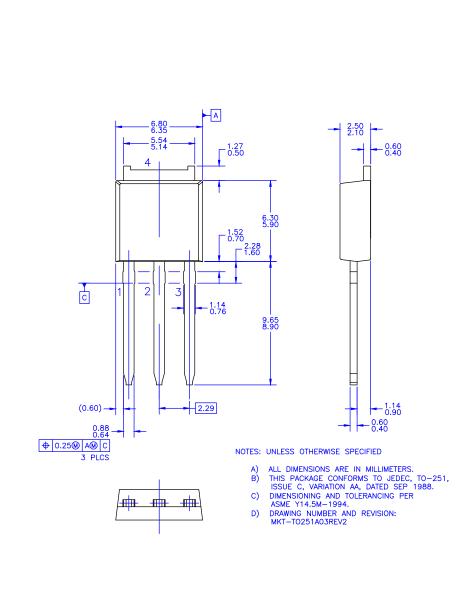


Figure 9. TO-251 3L (IPAK)

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